

Description

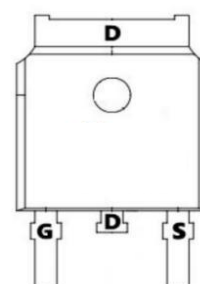
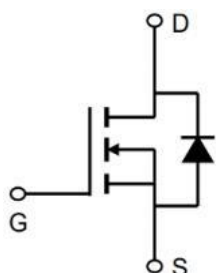
The SX5N20D-H is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features

VDS =200V, ID =5A
RDS(ON) <600mΩ@ VGS=10V

Application

Uninterruptible Power Supply(UPS)
Power Factor Correction (PFC)



Absolute Maximum Ratings $T_c = 25^\circ\text{C}$, unless otherwise noted

Symbol	Parameter	Value	Unit
VDSS	Drain-Source Voltage ($V_{GS} = 0V$)	200	V
I_D	Continuous Drain Current	5	A
IDM	Pulsed Drain Current	20	A
VGSS	Gate-Source Voltage	± 20	V
EAS	Single Pulse Avalanche Energy	45	mJ
IAR	Avalanche Current	3	A
EAR	Repetitive Avalanche Energy	3.2	mJ
P_D	Power Dissipation ($T_c = 25^\circ\text{C}$)	46	W
RthJC	Thermal Resistance, Junction-to-Case	2.7	$^\circ\text{C/W}$
RthJA	Thermal Resistance, Junction-to-Ambient	60	$^\circ\text{C/W}$
TJ, Tstg	Operating Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	200	221	--	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V, T _J = 25°C	--	--	5	μA
IDSS		V _{DS} = 160V, V _{GS} = 0V, T _J = 125°C	--	--	100	
IGSS	Gate-Source Leakage	V _{GS} = ±20V	--	--	±100	nA
VGS(th)	Gate-Source Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.5	3.1	4.0	V
RDS(on)	Drain-Source On-Resistance (Note3)	V _{GS} = 10V, I _D = 2.5A	--	530	600	mΩ
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	228	--	pF
C _{oss}	Output Capacitance		--	48	--	
C _{rss}	Reverse Transfer Capacitance		--	17	--	
Q _g	Total Gate Charge	V _{DD} = 160V, I _D = 5.0A, V _{GS} = 10V	--	18	--	nC
Q _{gs}	Gate-Source Charge		--	1.5	--	
Q _{gd}	Gate-Drain Charge		--	9.5	--	
td(on)	Turn-on Delay Time	V _{DD} = 100V, I _D = 5.0A, R _G = 25 Ω	--	10	--	ns
t _r	Turn-on Rise Time		--	19	--	
td(off)	Turn-off Delay Time		--	43	--	
t _f	Turn-off Fall Time		--	32	--	
I _S	Continuous Body Diode Current	T _C = 25 °C	--	--	5	A
ISM	Pulsed Diode Forward Current		--	--	20	
V _{SD}	Body Diode Voltage	T _J = 25°C, I _{SD} = 5A, V _{GS} = 0V	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 5A, di _F /dt = 100A/μs	--	160	--	ns
Q _{rr}	Reverse Recovery Charge		--	1.5	--	μC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The EAS data shows Max. rating . I_{AS} = 3A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25 °C
- 3、The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

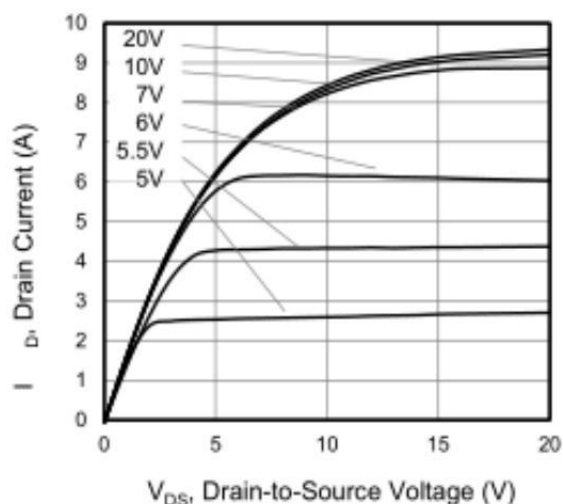


Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

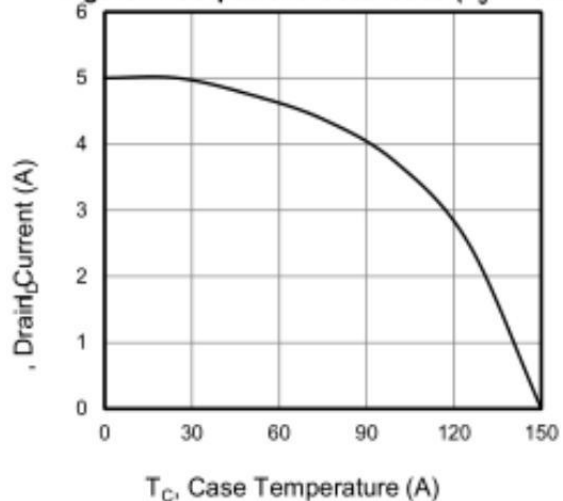


Figure 3. Drain Current vs. Temperature

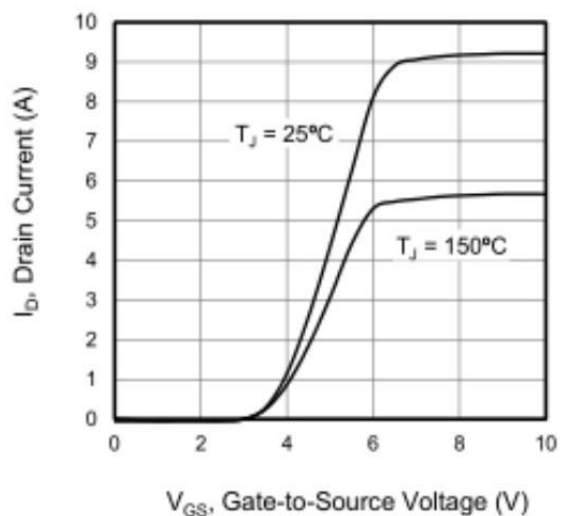


Figure 5. Transfer Characteristics

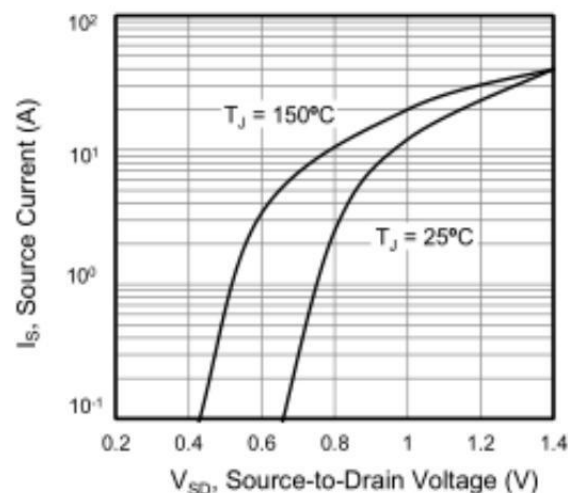


Figure 2. Body Diode Forward Voltage

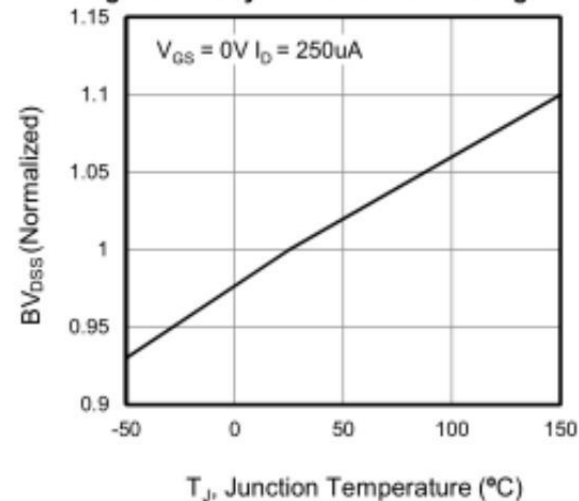


Figure 4. BV_{DSS} Variation vs. Temperature

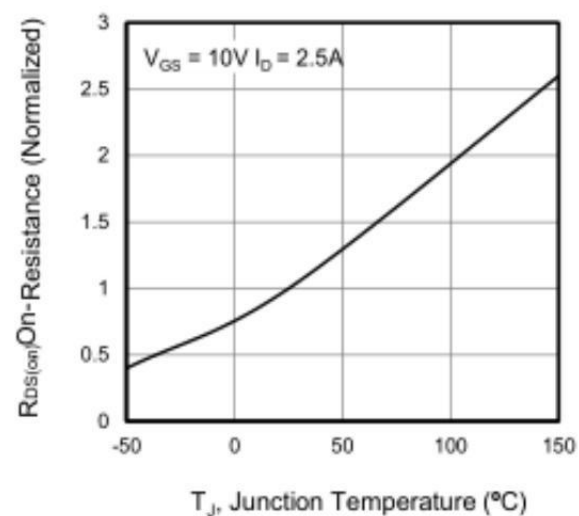


Figure 6. On-Resistance vs. Temperature

Typical Characteristics

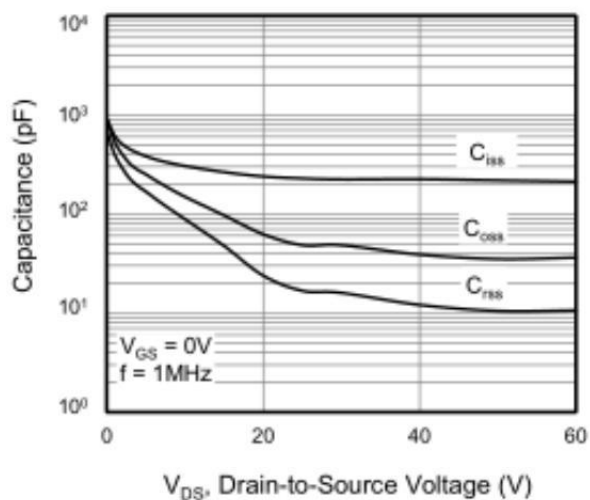


Figure 7. Capacitance

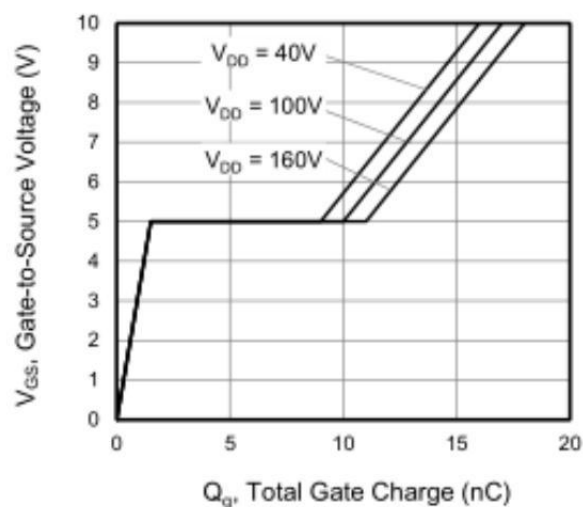


Figure 8. Gate Charge

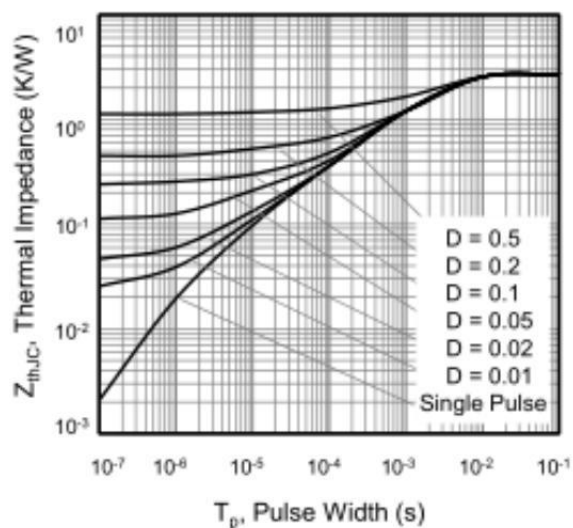
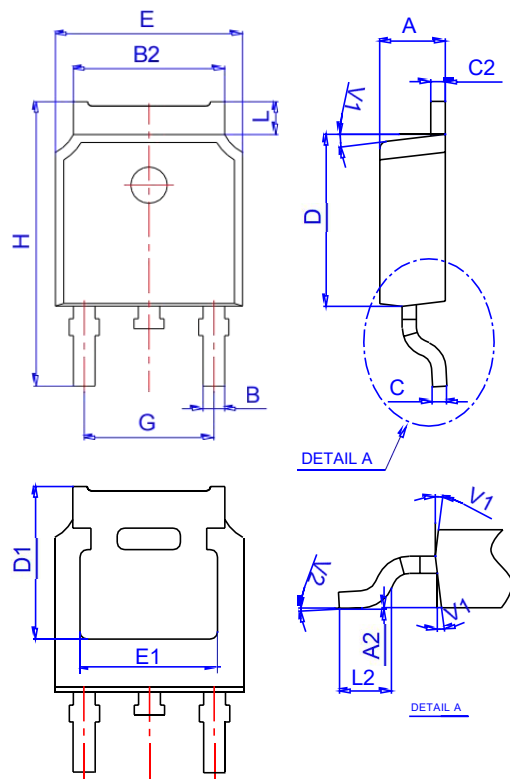


Figure 10. Transient Thermal Impedance

Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500